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L15 ANSWER 7 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN
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2001:225359 HCAPLUS AN

134:246133 DN

A method and apparatus for integrating a metal nitride film in a ΤI semiconductor device

Narwankar, Pravin; Sahin, Turgut IN

Applied Materials, Inc., USA PA

Eur. Pat. Appl., 16 pp. SO CODEN: EPXXDW

DT Patent

English LA

ICM H01L021-285 IC

76-3 (Electric Phenomena) CC

FA	N.CNT 1 PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
ΡI	EP 1087430 US 6337289 SG 83817 TW 477027 JP 2001148380 US 2002055270 US 6518203	A2 B1 A1 B A2 A1 B2	20010328 20020108 20011016 20020221 20010529 20020509 20030211	EP 2000-308405 US 1999-405554 SG 2000-5483 TW 2000-89119691 JP 2000-290804 US 2001-2654	20000925 19990924 20000922 20000922 20000925 20011018
PR	AT US 1999-405554	Α	19990924		

PRAI US 1999-405554 The present invention describes a method of processing a substrate. According to the present invention a dielec. layer is formed on the substrate. The dielec. layer is then exposed in a 1st chamber to activated N atoms formed in a 2nd chamber to form a N passivated dielec. layer. A metal nitride film is then formed on the N passivated dielec.

layer. RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical

process); PROC (Process); USES (Uses) (for integrating metal nitride film in semiconductor device)

172901-22-3 HCAPLUS RN

Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, CN (OC-6-23)- (9CI) (CA INDEX NAME)

